



DMG2307LQ

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	90mΩ @ V <sub>GS</sub> = -10V	-3.8A
-30V	134mΩ @ V <sub>GS</sub> = -4.5V	-3.1A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Load Switch for Portable Devices

## **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

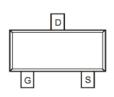
#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.08 grams (Approximate)

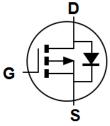




Top View



Top View



Equivalent Circuit

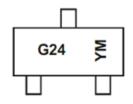
### **Ordering Information (Note 5)**

Ī	Part Number	Case	Packaging
	DMG2307LQ-7	SOT23	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



G24 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	202	22   20	23	2024	2025	2026	2027	2028
Code	F	G	Н	ı	J		<	L	M	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	l <sub>D</sub>	-2.5 -2.0	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-3.8 -3.0	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	t ≦10sec	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-4.6 -3.6	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-3.1 -2.5	А
Pulsed Drain Current (Note 7)	•		I <sub>DM</sub>	-20	A

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	0.76	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	159	°C/W
Total Power Dissipation (Note 7)	PD	1.36	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	94	°C/W
Total Power Dissipation (Note 7) t ≤ 10sec	P <sub>D</sub>	1.9	W
Thermal Resistance, Junction to Ambient (Note 7) t ≤ 10sec	$R_{\theta JA}$	65.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

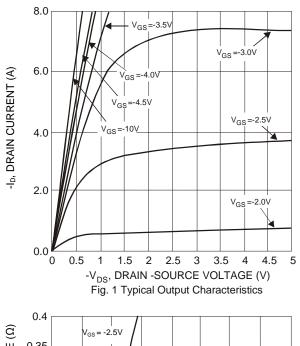
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	@T <sub>C</sub> = +25°C	I <sub>DSS</sub>		_	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage		I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)				•	•		
Gate Threshold Voltage		V <sub>GS(TH)</sub>	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance			_	70	90	mΩ	$V_{GS} = -10V, I_D = -2.5A$
Static Drain-Source On-Resistance		R <sub>DS(ON)</sub>	_	105	134	11177	$V_{GS} = -4.5V, I_D = -2.5A$
Forward Transfer Admittance		Y <sub>fs</sub>	_	4.8	_	S	$V_{DS} = -10V, I_{D} = -2.5A$
Diode Forward Voltage		V <sub>SD</sub>		-0.75	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)				•	•		
Input Capacitance		C <sub>iss</sub>	_	371.3	_	pF	45)/ )/ 0)/
Output Capacitance		Coss	_	51.3	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	45.9	_	pF	T = 1.0WHZ
Gate Resistance		$R_g$		17	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)		Qg	_	4.0	_	nC	
Total Gate Charge (V <sub>GS</sub> = -10V)		Qg		8.2	_	nC	$V_{GS} = -10V, V_{DS} = -15V,$
Gate-Source Charge		Q <sub>gs</sub>		0.9	_	nC	$I_D = -3A$
Gate-Drain Charge		Q <sub>qd</sub>		1.2	_	nC	
Turn-On Delay Time		t <sub>D(ON)</sub>		4.8	_	ns	
Turn-On Rise Time		t <sub>R</sub>	_	7.3	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time		t <sub>D(OFF)</sub>	_	22.4	_	ns	$R_L = 15\Omega$ , $R_G = 6\Omega$ ,
Furn-Off Fall Time		t <sub>F</sub>	_	13.4	_	ns	$I_D = -1A$

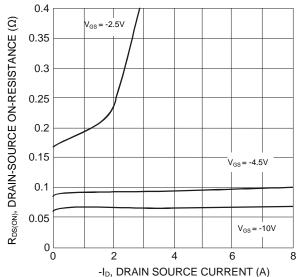
Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.









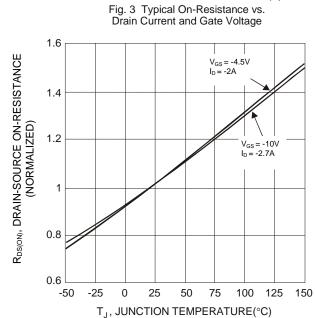
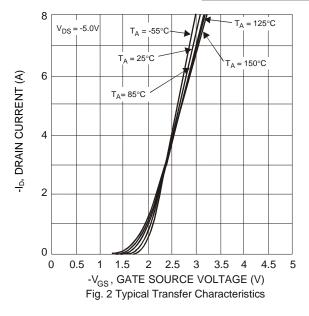
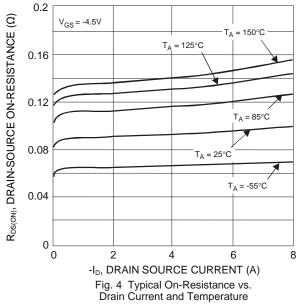


Fig. 5 On-Resistance Variation with Temperature





0.2 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.16 V<sub>GS</sub>= -4.5V I<sub>D</sub> = -2A 0.12 0.08 V<sub>GS</sub>= -10V  $I_{D} = -2.7A$ 0.04 -25 -50 25 75 100 125 150 50 T<sub>J</sub>, JUNCTION TEMPERATURE(°C)

Fig. 6 On-Resistance Variation with Temperature





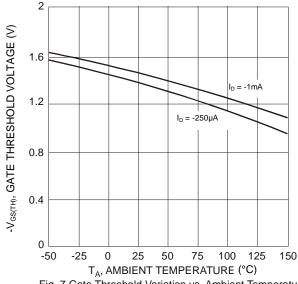
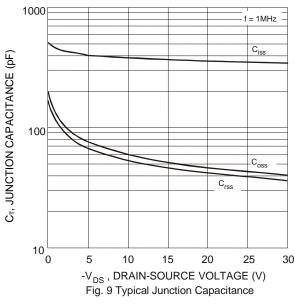
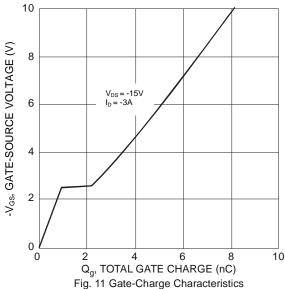
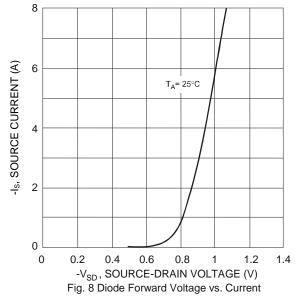


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







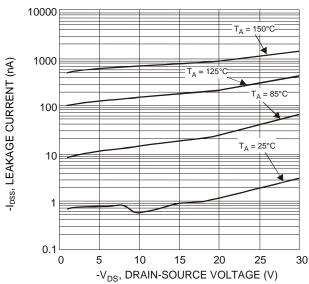
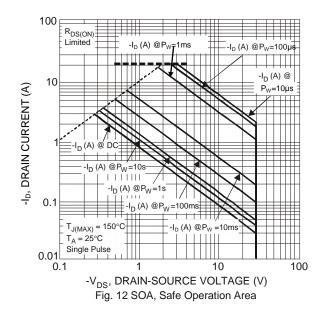
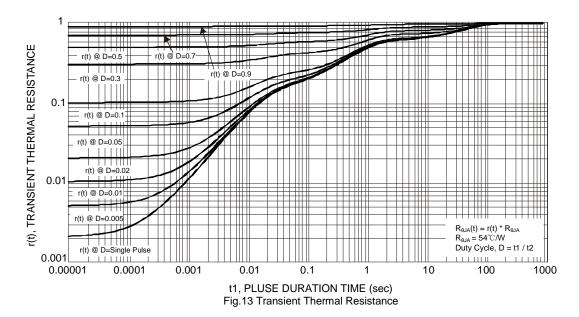


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage





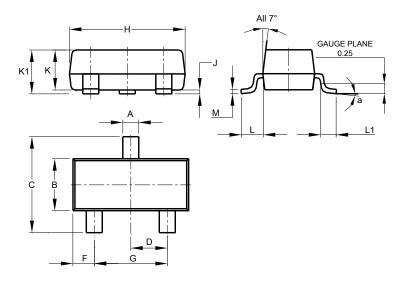




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

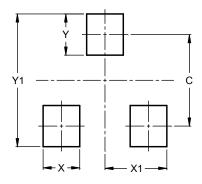


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
Х	8.0
X1	1.35
Y	0.9
Y1	2.0



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